

## General Description

The WSD50P10DN56 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the synchronous buck converter applications.

The WSD50P10DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

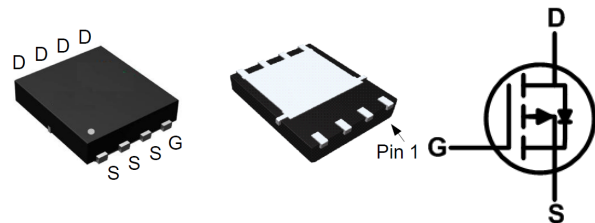
## Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
-100V	40mΩ	-34A

## Applications

- Power Management for Industrial DC / DC Converters.

## DFN5X6 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-34	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-22	A
I <sub>DM</sub>	Pulsed Drain Current	-136 <sup>a</sup>	A
E <sub>AS</sub> <sup>c</sup>	Single Pulse Avalanche Energy	182	mJ
I <sub>AS</sub> <sup>c</sup>	Avalanche Current	-27	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	96	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub> <sup>b</sup>	Thermal Resistance Junction-Ambient	---	60	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case	---	1.3	°C/W

Note a : Pulse width is limited by max. junction temperature.

Note b : Surface Mounted on 1in<sup>2</sup> pad area.

Note c : UIS tested and pulse width are limited by maximum junction temperature 150°C(initial temperature T<sub>J</sub>=25°C).

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-100	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.021	---	V/°C
R <sub>DS(ON)</sub> <sup>d</sup>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-18A	---	32	40	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	---	38	51	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-2.0	-3.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.08	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-80V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	-30	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Q <sub>g</sub> <sup>e</sup>	Total Gate Charge	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-18A	---	56	---	nC
Q <sub>gs</sub> <sup>e</sup>	Gate-Source Charge		---	9.5	---	
Q <sub>gd</sub> <sup>e</sup>	Gate-Drain Charge		---	14.5	---	
T <sub>d(on)</sub> <sup>e</sup>	Turn-On Delay Time	V <sub>DD</sub> =-30V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω, I <sub>D</sub> =-1A, RL=30Ω.	---	17	---	ns
T <sub>r</sub> <sup>e</sup>	Rise Time		---	9	---	
T <sub>d(off)</sub> <sup>e</sup>	Turn-Off Delay Time		---	83	---	
T <sub>f</sub> <sup>e</sup>	Fall Time		---	34	---	
C <sub>iss</sub> <sup>e</sup>	Input Capacitance	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V, f=1MHz	---	2480	3207	pF
C <sub>oss</sub> <sup>e</sup>	Output Capacitance		---	268	---	
C <sub>riss</sub> <sup>e</sup>	Reverse Transfer Capacitance		---	126	---	

**Diode Characteristics**

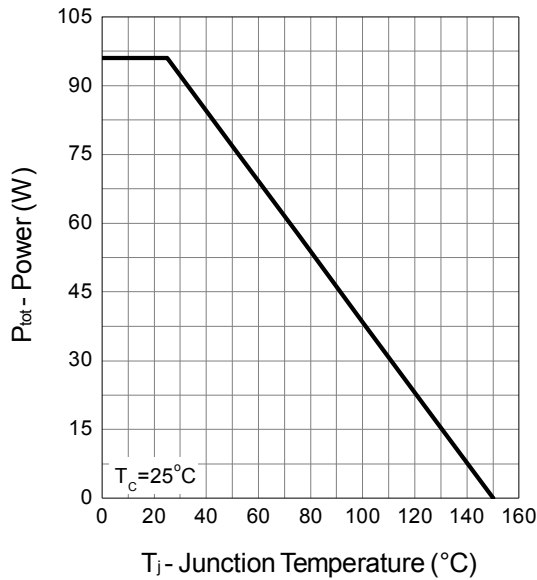
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-18	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-18A, T <sub>J</sub> =25°C	---	---	-1.2	V

Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.

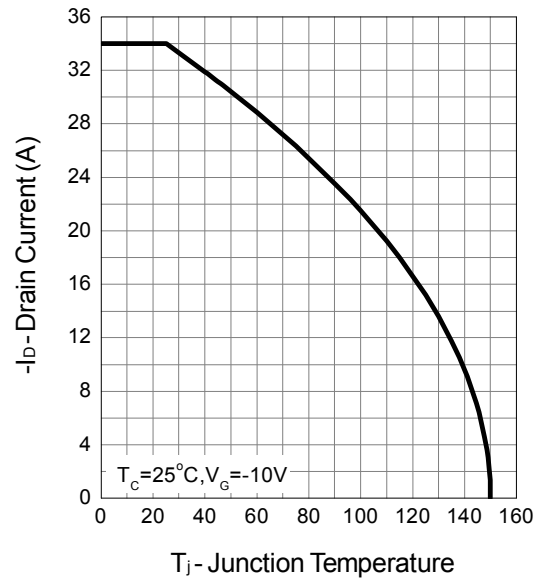
Note e : Guaranteed by design, not subject to production testing.

**Typical Characteristics**

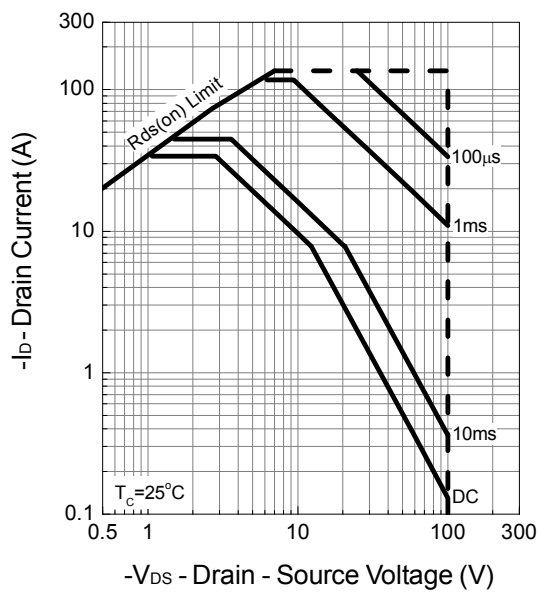
**Power Dissipation**



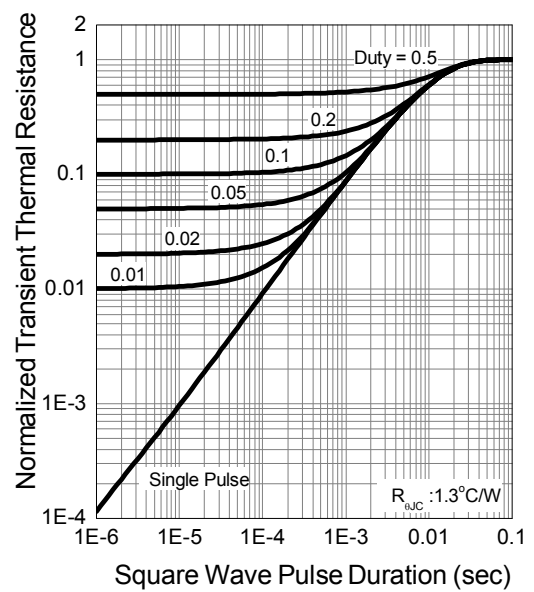
**Drain Current**



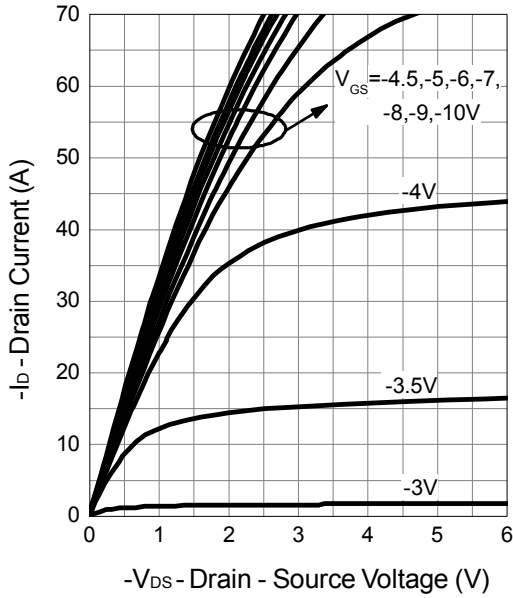
**Safe Operation Area**



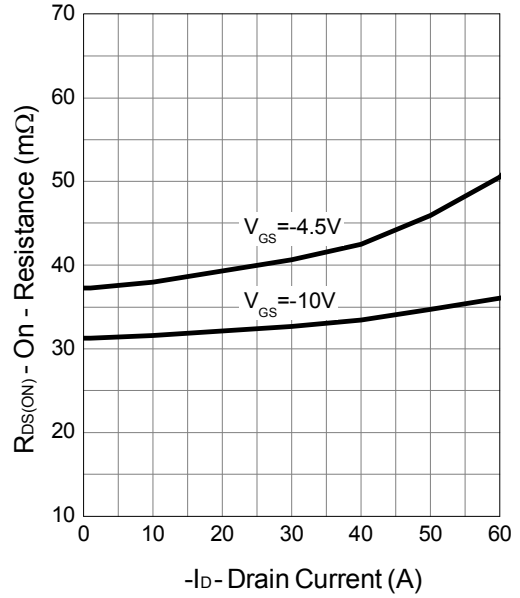
**Thermal Transient Impedance**



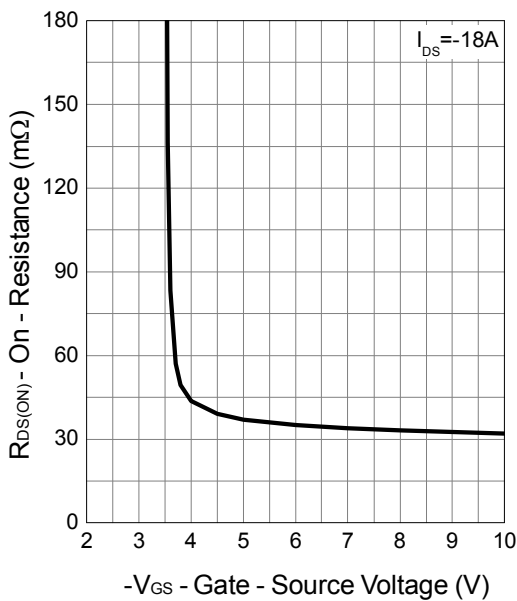
**Output Characteristics**



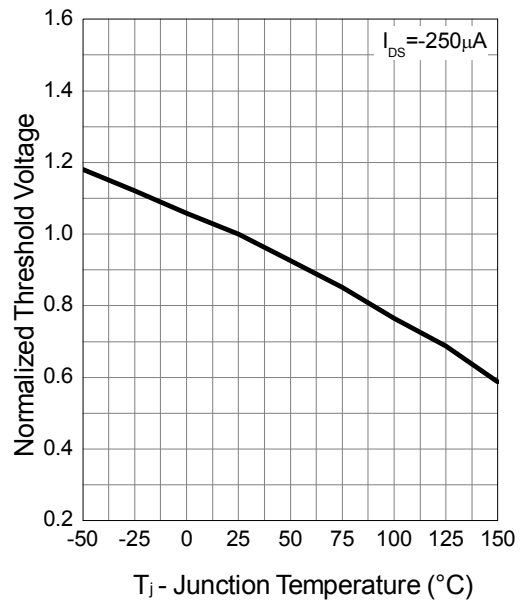
**Drain-Source On Resistance**



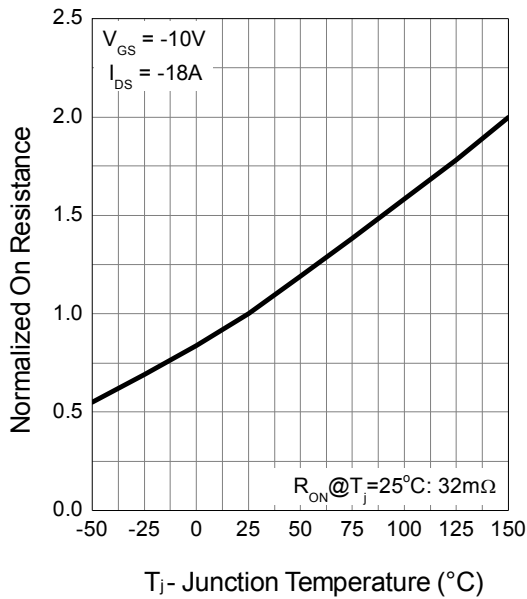
**Gate-Source On Resistance**



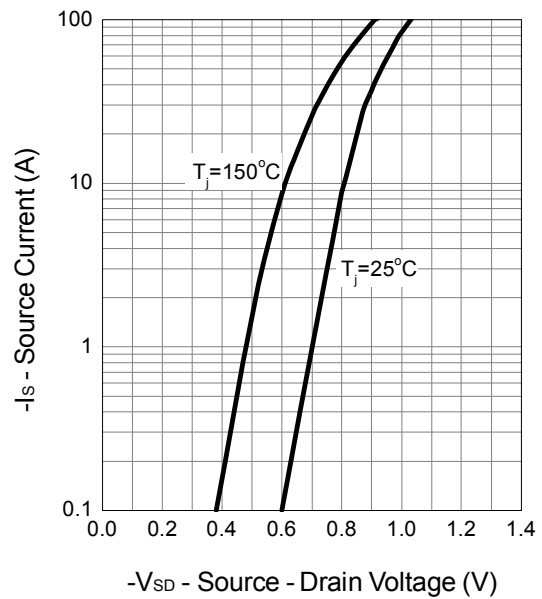
**Gate Threshold Voltage**



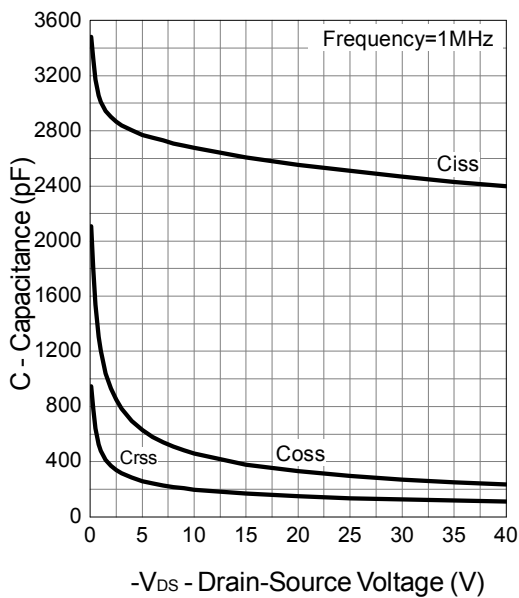
**Drain-Source On Resistance**



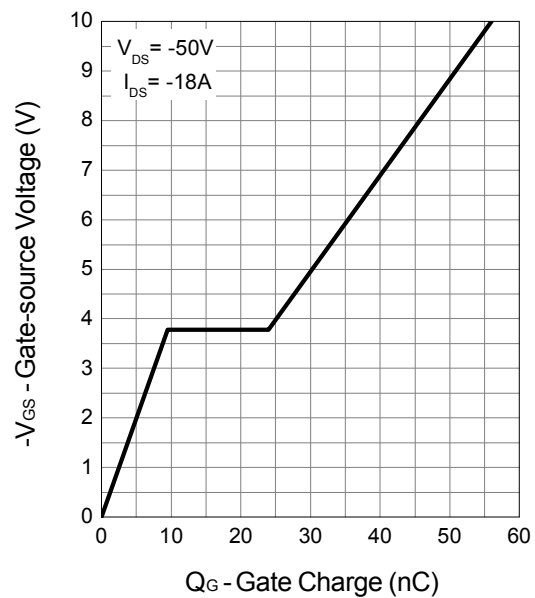
**Source-Drain Diode Forward**



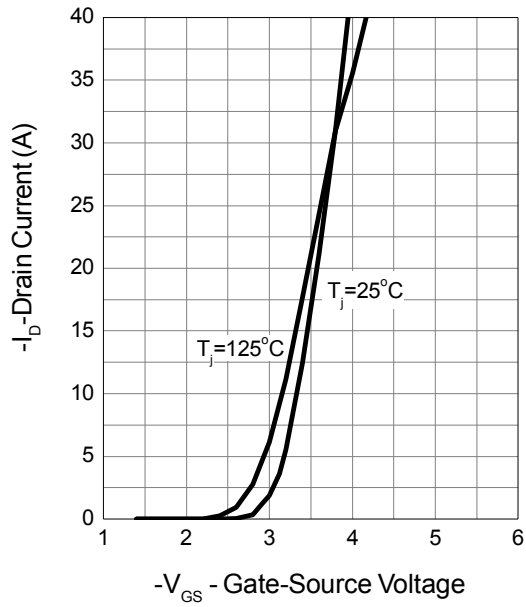
**Capacitance**



**Gate Charge**



**Transfer Characteristics**



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